22/10/12 V1.0

multicomp





**Pin Configuration** 

- 1. Emitter
- 2. Base
- 3. Collector

# Features:

- · Devices with breakdown voltages of 160V minimum
- NPN Silicon High Voltage Power Transistors

# **Absolute Maximum Ratings:**

### (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit	
Collector Base Voltage	V <sub>CBO</sub> 300			
Collector Emitter Voltage	V <sub>CES</sub>	300	V	
Emitter-Base Voltage	V <sub>EBO</sub>	5		
Collector Current Continuous	Ι <sub>c</sub>	100	•	
Collector Current-Peak	I <sub>CM</sub>	300	A	
Power Dissipation at $T_a = 25^{\circ}C$ Derate above 25°C	D	1 5.7	W	
Power Dissipation at T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	5 28.57	mW/°C	
Operating Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-65 to +200	°C	
Thermal Resistance				
Junction to Ambient in Free Air	R <sub>th(j-a)</sub> 175		°C/W	
Junction to Case	R <sub>th(j-c)</sub>	35	C/W	

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## **Electrical Characteristics:**

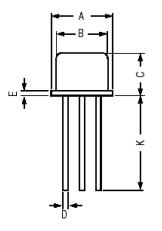
(T<sub>a</sub> = +25°C unless otherwise specified)

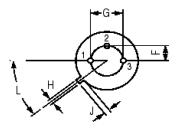
Parameter	Symbol	Test Condition		Unit
Collector Emitter Voltage	V <sub>CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	>300	
Collector Base Voltage	V <sub>CBO</sub>	I <sub>C</sub> = 100μΑ, I <sub>E</sub> = 0	>300	V
Emitter Base Voltage	V <sub>EBO</sub>	I <sub>E</sub> = 100μΑ, I <sub>C</sub> = 0	>5	
Collector Cut off Current	I <sub>CBO</sub>	V <sub>CBO</sub> = 250V, I <sub>E</sub> = 0	<50	nA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> = 30mA, V <sub>CE</sub> = 10V	25	-
Collector Emitter Saturation Voltage	V <sub>CE(Sat)</sub>	I <sub>C</sub> = 30mA, I <sub>B</sub> = 6mA	1	V

#### **Dynamic Characteristics**

Transition Frequency	f <sub>t</sub>	I <sub>C</sub> = 15mA, V <sub>CE</sub> = 10V, f = 100MHz	75	MHz
Collector Base Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0, f = 1MHz	2.5	рF

# TO-39 Metal Can Package





Dim.	Min.	Max.
A	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42°	48°
Dimensione : Millimetree		

Dimensions : Millimetres

#### **Pin Configuration**

- 1. Emitter
- 2. Base
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# Part Number Table

Description	Part Number	
Transistor, NPN, TO-39	BF259	

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